

**SIEMENS**

# LH 1485

## OPTICALLY COUPLED HIGH SPEED MOSFET DRIVERS OPTOCOUPLER

**FEATURES**

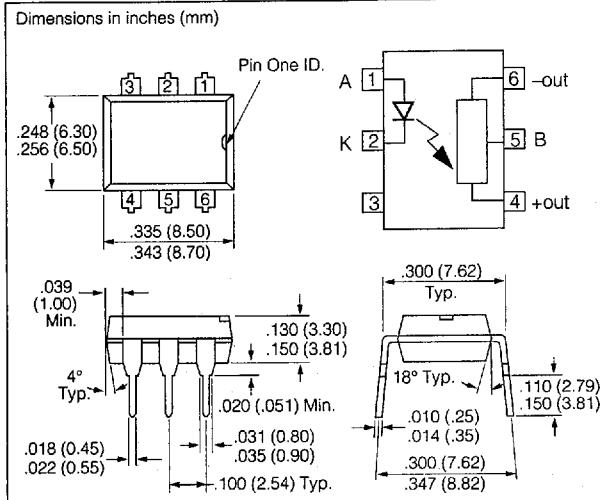
- Fast Turn On
- Fast Turn Off
- Low Input Current
- Isolation Test Voltage, 5300 VAC<sub>RMS</sub>

**APPLICATIONS**

- Motor Drive Controls
- IGBT-predrivers
- AC/DC Power Inverters

**DESCRIPTION**

The LH1485 is a photovoltaic generator (optically coupled) designed to drive highly capacitive loads such as the gate of a power MOSFET transistor and at the same time provide isolation and floating voltage supply capability. The coupler consists of a GaAlAs light emitting diode as input control and a custom photo IC chip with photodiode array (PDA) as output device. When the LED is turned on, the emitted light produces a voltage in the PDA. The output of the PDA is used to drive the gate of a power MOSFET. The photo IC chip contains additional circuitry to enhance the switching speeds, (both turn on turn off). The optocoupler is packaged in a 6 pin DIP.

**Maximum Ratings****Emitter**

Reverse Voltage .....	4 V
Forward Current .....	60 mA
Peak Forward Current.....	600 mA
Power Dissipation.....	100 mW
Thermal Resistance.....	700°C/W

**Detector**

Breakdown Voltage (pin 5 to 6) .....	300 V
Peak Input Current (pin 5 to 4) .....	50 mA
Reverse Current (pin 5 to 6, V=100 V) .....	200 nA
Power Dissipation (pin 5 to 4) .....	150 mW

**Package**

Insulation Thickness between Emitter and Detector .....	≥0.4 mm
Isolation Test Voltage (1 sec.).....	5300 VAC <sub>RMS</sub>

**Isolation Resistance**

$V_{IO}=500$ V, $T_A=25^\circ\text{C}$ .....	$\geq 10^{12} \Omega$
$V_{IO}=500$ V, $T_A=100^\circ\text{C}$ .....	$\geq 10^{11} \Omega$

**Comparative Tracking Index per**

DIN IEC 112/VDE 303, Part 1.....	≥175
Total Power Dissipation .....	250 mW
Storage Temperature Range .....	-55°C to +150°C
Operating Temperature Range.....	-55°C to +100°C
Junction Temperature.....	100°C

Soldering Temperature (max. 10 sec.,

dip soldering distance to seating plane &gt;1.5 mm)..... 260°C

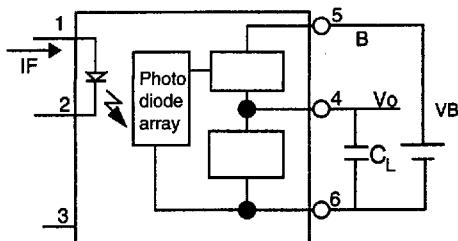
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**Electrical Characteristics**

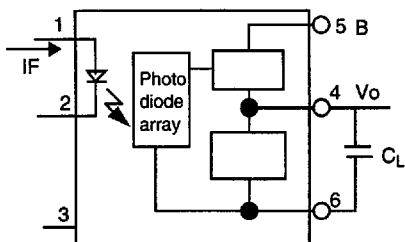
Parameter	Symbol	Min.	Typ.	Max.	Unit	Condition
<b>Input — Emitter</b>						
LED Forward Voltage	V <sub>F</sub>	0.9	1.5	2.1	V	I <sub>F</sub> =10 mA
LED Junction Capacitance	C <sub>J</sub>		25		pF	V <sub>R</sub> =0 V, f=1 MHz
<b>MOSFET Driver Output with External Biasing (see Figure 1 and Figure 3)</b>						
Zener Voltage (pin 4 to 6)	V <sub>Z</sub>		13		V	I <sub>ZT</sub> =10 µA
Dynamic Output Voltage (pin 4 to 6)	V <sub>OUT</sub>	9	11		V	C <sub>L</sub> =2000 pF, V <sub>B</sub> =20 V, I <sub>F</sub> =10 mA
Dynamic Output Current (pin 4 to 6)	I <sub>OUT</sub>		5		mA	C <sub>L</sub> =2000 pF, V <sub>B</sub> =20 V, I <sub>F</sub> =10 mA
			15			C <sub>L</sub> =2000 pF, V <sub>B</sub> =20 V, I <sub>F</sub> =40 mA
Dynamic Output Resistance	R <sub>OUT</sub>		300		Ω	I <sub>F</sub> =10 mA
			20			
Turn-on Time	t <sub>ON</sub>		3.5	5	µs	C <sub>L</sub> =2000 pF, I <sub>F</sub> =40 mA Measure at V <sub>OUT</sub> =5 V, V <sub>B</sub> =20 V
Turn-off Time	t <sub>OFF</sub>		3.5	5	µs	C <sub>L</sub> =2000 pF, I <sub>F</sub> =40 mA Measure at V <sub>OUT</sub> =2 V, V <sub>B</sub> =20 V
<b>MOSFET Driver Output without External Biasing (see Figure 2 and Figure 3)</b>						
Output Open Circuit Voltage (pin 4 to 6)	V <sub>OC</sub>	8	10		V	I <sub>F</sub> =10 mA
Output Short Circuit Current (pin 4 to 6)	I <sub>SC</sub>	2.1	4		µA	I <sub>F</sub> =10 mA
		8.4	16			
Dynamic Output Resistance Sinking (pin 4)	R <sub>OUT</sub>		20		Ω	I <sub>F</sub> =10 mA
Turn-on Time	t <sub>ON</sub>		650	1000	µs	C <sub>L</sub> =2000 pF (see Figure 3) Measure at V <sub>OUT</sub> =5 V, I <sub>F</sub> =40 mA
Turn-off Time	t <sub>OFF</sub>		3	5	µs	C <sub>L</sub> =2000 pF (see Figure 3) Measure at V <sub>OUT</sub> =2 V, I <sub>F</sub> =40 mA
<b>MOSFET Driver Output Switching Speed (see Figure 3, Figure 4, Figure 5)</b>						
Rise time	t <sub>R</sub>		500		ns	M1 C <sub>GS</sub> =2000 pF, V <sub>S</sub> =50 V Measure at 90%–10% M1 V <sub>DS</sub> (see Figure 4)
Turn-on Time	t <sub>ON</sub>		3.5		µs	
Fall time	t <sub>F</sub>		300		ns	
Turn-off Time	t <sub>OFF</sub>		3.5		µs	
<b>Package Isolation Characteristics</b>						
Input-Output CMRR	dv/dt		15 kV		V/µs	V <sub>CM</sub> =1000 V
Coupling Capacitance	C <sub>IO</sub>		1		pF	f=1 MHz

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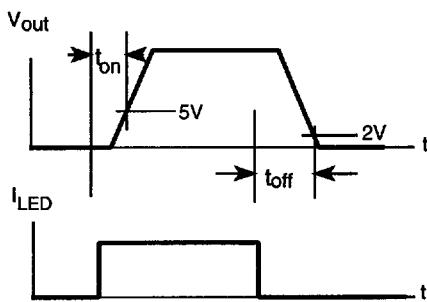
**Figure 1. Switching time measurement with external voltage bias**



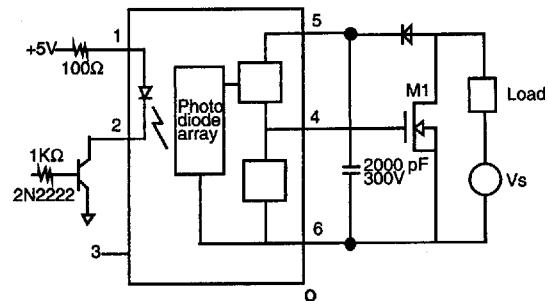
**Figure 2. Switching time measurement**



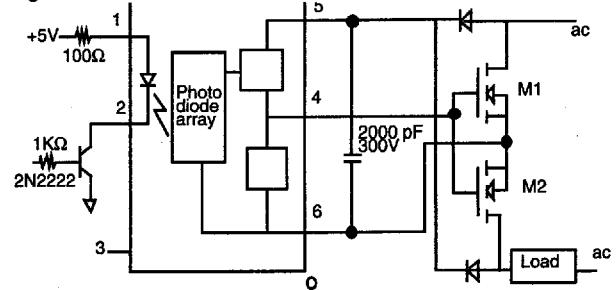
**Figure 3. IL485 connected in AC load switching configuration**



**Figure 4. Switching time measurement without voltage bias**



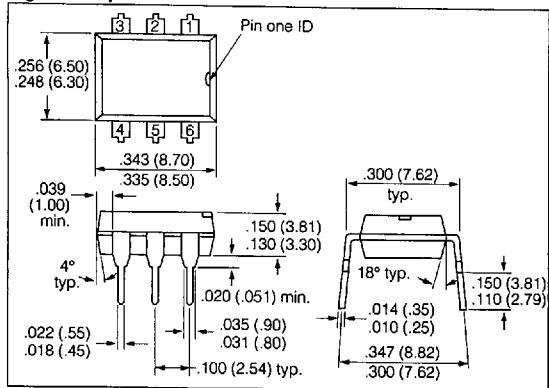
**Figure 5. IL485 connected in DC load switching configuration**



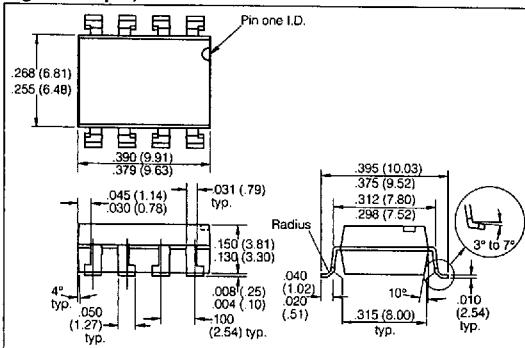
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## Package Outline Dimensions

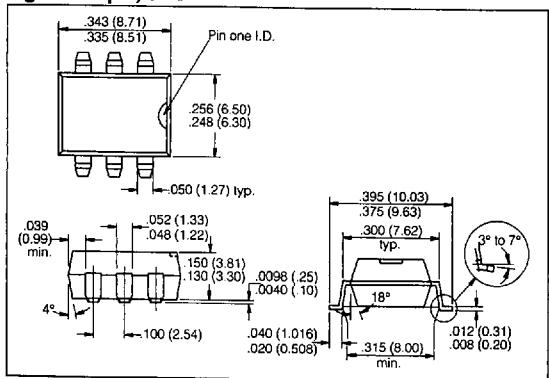
**Figure 1. 6-pin DIP**



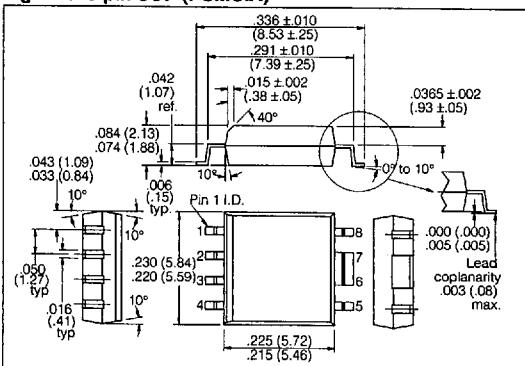
**Figure 4. 8-pin, SMD**



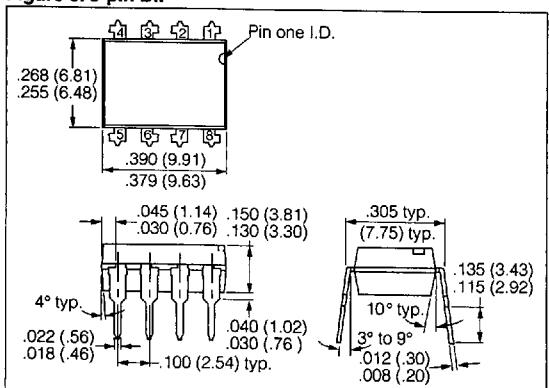
**Figure 2. 6-pin, SMD**



**Figure 5. 8-pin SOP (PCMCIA)**



**Figure 3. 8-pin DIP**



**Figure 6. 18-pin SOP (PCMCIA)**

